

# RGTH60TS65

#### 650V 30A Field Stop Trench IGBT

V <sub>CES</sub>	650V
I <sub>C(100°C)</sub>	30A
V <sub>CE(sat) (Typ.)</sub>	1.6V
$P_D$	194W

#### ● Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

#### Applications

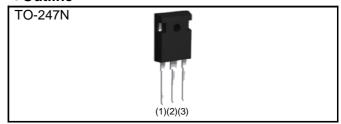
**PFC** 

**UPS** 

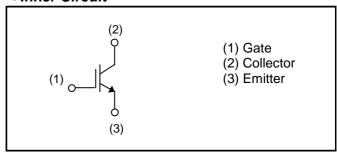
**Power Conditioner** 

ΙH

#### Outline



#### ●Inner Circuit



Packaging Specifications

	<del>0                                    </del>	
	Packaging	Tube
	Reel Size (mm)	-
Type	Tape Width (mm)	-
Type	Basic Ordering Unit (pcs)	450
	Taping Code	C11
	Marking	RGTH60TS65

### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	650	V
Gate - Emitter Voltage		$V_{GES}$	±30	V
Collector Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	58	А
	T <sub>C</sub> = 100°C	I <sub>C</sub>	30	А
Pulsed Collector Current		I <sub>CP</sub> *1	120	А
Power Dissipation	$T_C = 25^{\circ}C$	$P_{D}$	194	W
	T <sub>C</sub> = 100°C	$P_{D}$	97	W
Operating Junction Temperature		T <sub>j</sub>	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>jmax</sub>.

#### ●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	ı	0.77	°C/W

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ai nietei	Syllibol		Min.	Тур.	Max.	Onit
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_C = 10 \mu A, V_{GE} = 0 V$	650	-	ı	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 650V, V_{GE} = 0V$	1	-	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V$ , $V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 21.0 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C = 30A$ , $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.6 2.1	2.1 -	V

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Dorometer	Symbol	Conditions	Values			Unit
Parameter			Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V	-	1670	-	
Output Capacitance	C <sub>oes</sub>	$V_{GE} = 0V$	-	66	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	27	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 300V	-	58	-	
Gate - Emitter Charge	$Q_{ge}$	I <sub>C</sub> = 30A	-	15	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	20	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 30A, V_{CC} = 400V$	-	27	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	40	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 25°C	-	105	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	47	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 30A, V_{CC} = 400V$	-	27	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	40	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 175°C	-	120	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	59	-	
		I <sub>C</sub> = 120A, V <sub>CC</sub> = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

Fig.1 Power Dissipation vs. Case Temperature

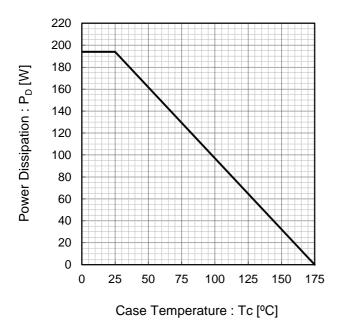


Fig.2 Collector Current vs. Case Temperature

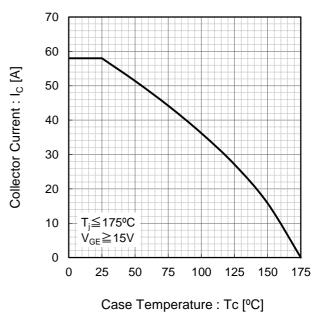
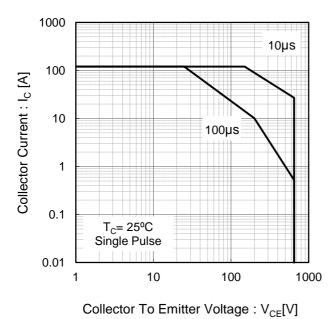


Fig.3 Forward Bias Safe Operating Area



Collector Current : I<sub>c</sub> [A]

160
140
120
100
80
60
40
20
T<sub>j</sub>≤175°C
V<sub>GE</sub>=15V
0
0
200
400
600
800

Fig.4 Reverse Bias Safe Operating Area

Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.5 Typical Output Characteristics

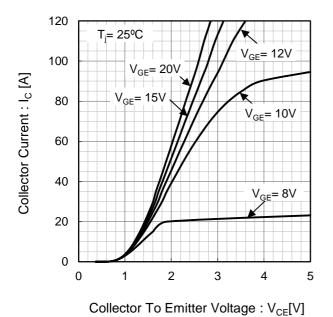
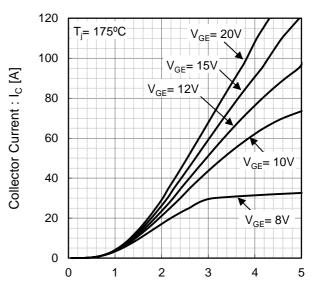


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.7 Typical Transfer Characteristics

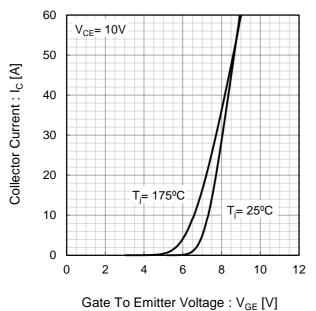


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

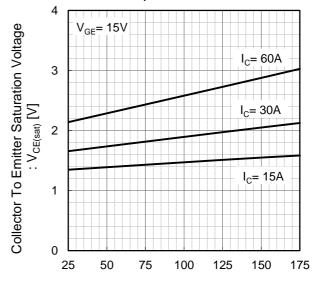


Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

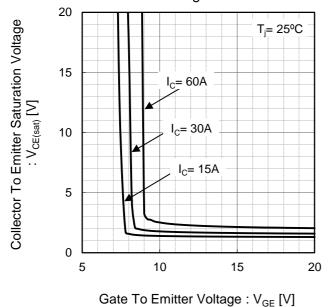
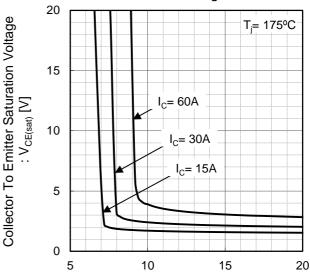


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V<sub>GE</sub> [V]

Fig.11 Typical Switching Time vs. Collector Current

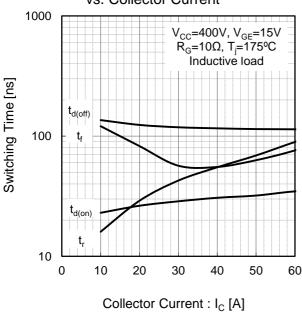
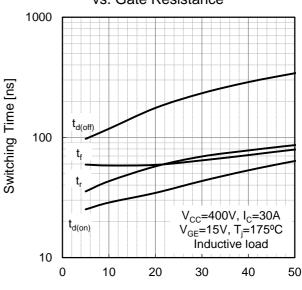


Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance :  $R_G[\Omega]$ 

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1  $\mathsf{E}_{\mathsf{off}}$ 0.1  $V_{CC}$ =400V,  $V_{GE}$ =15V  $R_{G}$ =10 $\Omega$ ,  $T_{j}$ =175°C Inductive load 0.01 0 10 20 40 50 60 30 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 0.1  $V_{CC}$ =400V,  $I_{C}$ =30A  $V_{GE}$ =15V,  $T_{j}$ =175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz  $V_{GE}=0V$ 0.01 0.1 1 10 100 Collector To Emitter Voltage : V<sub>CE</sub>[V]

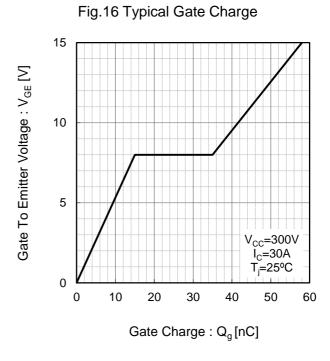
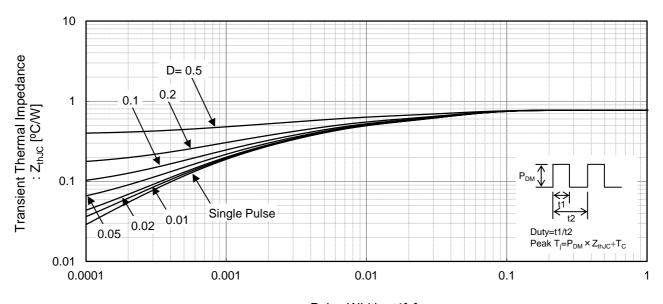


Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

### •Inductive Load Switching Circuit and Waveform

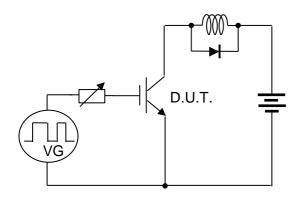


Fig.18 Inductive Load Circuit

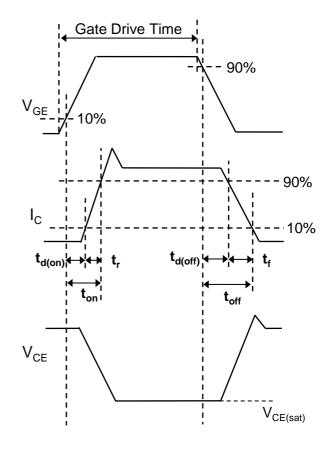


Fig.19 Inductive Load Waveform

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